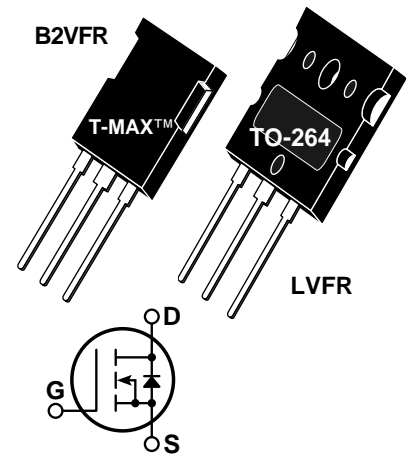


POWER MOS V®
FREDFET


Power MOS V® is a new generation of high voltage N-Channel enhancement mode power MOSFETs. This new technology minimizes the JFET effect, increases packing density and reduces the on-resistance. Power MOS V® also achieves faster switching speeds through optimized gate layout.

- **Identical Specifications: T-MAX™ or TO-264 Package**
- **Lower Leakage**
- **Fast Recovery Body Diode**
- **Faster Switching**
- **100% Avalanche Tested**

MAXIMUM RATINGS

 All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT20M18	UNIT
V_{DSS}	Drain-Source Voltage	200	Volts
I_D	Continuous Drain Current @ $T_C = 25^\circ\text{C}$ ⑤	100	Amps
I_{DM}	Pulsed Drain Current ① ⑤	400	
V_{GS}	Gate-Source Voltage Continuous	± 30	Volts
V_{GSM}	Gate-Source Voltage Transient	± 40	
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	625	Watts
	Linear Derating Factor	5.0	W/°C
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300	
I_{AR}	Avalanche Current ① ⑤ (Repetitive and Non-Repetitive)	100	Amps
E_{AR}	Repetitive Avalanche Energy ①	50	mJ
E_{AS}	Single Pulse Avalanche Energy ④	3000	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 250\mu\text{A}$)	200			Volts
$I_{D(on)}$	On State Drain Current ② ⑤ ($V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10V$)	100			Amps
$R_{DS(on)}$	Drain-Source On-State Resistance ② ($V_{GS} = 10V, 0.5 I_{D[Cont.]}$)			0.018	Ohms
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = V_{DSS}, V_{GS} = 0V$)			250	μA
	Zero Gate Voltage Drain Current ($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$)			1000	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 30V, V_{DS} = 0V$)			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 2.5\text{mA}$)	2		4	Volts

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

DYNAMIC CHARACTERISTICS

APT20M18 B2VFR - LVFR

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C _{ISS}	Input Capacitance	V _{GS} = 0V		9910		pF
C _{OSS}	Output Capacitance	V _{DS} = 25V		2270		
C _{RSS}	Reverse Transfer Capacitance	f = 1 MHz		650		
Q _g	Total Gate Charge ③	V _{GS} = 10V		330		nC
Q _{GS}	Gate-Source Charge	V _{DD} = 0.5 V _{DSS}		75		
Q _{gd}	Gate-Drain ("Miller") Charge	I _D = I _D [Cont.] @ 25°C		143		
t _{d(on)}	Turn-on Delay Time	V _{GS} = 15V		18		ns
t _r	Rise Time	V _{DD} = 0.5 V _{DSS}		27		
t _{d(off)}	Turn-off Delay Time	I _D = I _D [Cont.] @ 25°C		54		
t _f	Fall Time	R _G = 0.6Ω		6		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I _S	Continuous Source Current (Body Diode)			100	Amps
I _{SM}	Pulsed Source Current ① (Body Diode)			400	
V _{SD}	Diode Forward Voltage ② (V _{GS} = 0V, I _S = -I _D [Cont.])			1.3	Volts
dv/dt	Peak Diode Recovery dv/dt ⑥			5	V/ns
t _{rr}	Reverse Recovery Time (I _S = -I _D [Cont.], di/dt = 100A/μs)	T _j = 25°C		230	ns
		T _j = 125°C		450	
Q _{rr}	Reverse Recovery Charge (I _S = -I _D [Cont.], di/dt = 100A/μs)	T _j = 25°C		0.9	μC
		T _j = 125°C		3.4	
I _{RRM}	Peak Recovery Current (I _S = -I _D [Cont.], di/dt = 100A/μs)	T _j = 25°C		11	Amps
		T _j = 125°C		20	

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
R _{θJC}	Junction to Case			0.20	°C/W
R _{θJA}	Junction to Ambient			40	

- ① Repetitive Rating: Pulse width limited by maximum T_j
- ② Pulse Test: Pulse width < 380 μs, Duty Cycle < 2%
- ③ See MIL-STD-750 Method 3471

- ④ Starting T_j = +25°C, L = 600μH, R_G = 25Ω, Peak I_L = 100A
- ⑤ The maximum current is limited by lead temperature.
- ⑥ I_S ≤ I_D [Cont.], di/dt = 100A/μs, V_R = 50V, T_j ≤ 150°C, R_G = 2.0Ω

APT Reserves the right to change, without notice, the specifications and information contained herein.

